

PolarHV™ HiPerFET IXFR 32N80P

Power MOSFET

ISOPLUS247™

(Electrically Isolated Back Surface)

N-Channel Enhancement Mode
Avalanche Rated
Fast Intrinsic Diode



$$V_{DSS} = 800 \text{ V}$$

$$I_{D25} = 20 \text{ A}$$

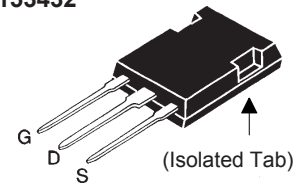
$$R_{DS(on)} \leq 290 \text{ m}\Omega$$

$$t_{rr} \leq 250 \text{ ns}$$

Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	800	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1 \text{ M}\Omega$	800	V
V_{GSS}	Continuous	± 30	V
V_{GSM}	Transient	± 40	V
I_{D25}	$T_C = 25^\circ\text{C}$	20	A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	70	A
I_{AR}	$T_C = 25^\circ\text{C}$	16	A
E_{AR}	$T_C = 25^\circ\text{C}$	50	mJ
E_{AS}	$T_C = 25^\circ\text{C}$	1.5	J
dv/dt	$I_S \leq I_{DM}$, $di/dt \leq 100 \text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 4 \Omega$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
F_C	Mounting force	20..120/4.5..26	N/lb
V_{ISOL}	50/60 Hz, RMS $t = 1$ minute	2500	V~
Weight		5	g

ISOPLUS247 (IXFR)

E153432



G = Gate D = Drain
S = Source

Features

- | Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- 2500V electrical isolation
- | Low drain to tab capacitance (<30pF)
- | Low $R_{DS(on)}$ HDMOS™ process
- | Rugged polysilicon gate cell structure
- | Rated for Unclamped Inductive Load Switching (UIS)
- | Fast intrinsic Rectifier

Applications

- | DC-DC converters
- | Battery chargers
- | Switched-mode and resonant-mode power supplies
- | DC choppers
- | AC motor control

Advantages

- | Easy assembly
- | Space savings
- | High power density

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, unless otherwise specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0 \text{ V}$, $I_D = 250 \mu\text{A}$	800		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 8 \text{ mA}$	3.0		5.0 V
I_{GSS}	$V_{GS} = \pm 30 \text{ V}_{DC}$, $V_{DS} = 0$			$\pm 200 \text{ nA}$
I_{DSS}	$V_{DS} = V_{DSS}$ $V_{GS} = 0 \text{ V}$ $T_J = 125^\circ\text{C}$			25 μA 1000 μA
$R_{DS(on)}$	$V_{GS} = 10 \text{ V}$, $I_D = I_T$ Pulse test, $t \leq 300 \mu\text{s}$, duty cycle $d \leq 2 \%$			290 $\text{m}\Omega$

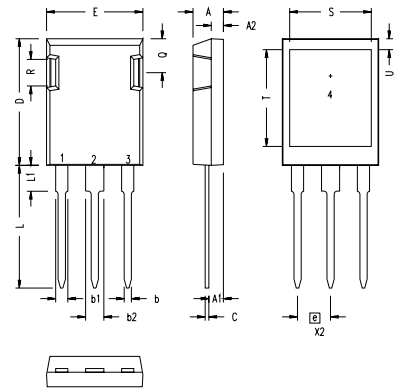
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
g_{fs}	$V_{DS} = 20\text{ V}; I_D = I_T$, pulse test	23	38	S
C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		8800	pF
C_{oss}			700	pF
C_{rss}			26	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$ (External)		30	ns
t_r			24	ns
$t_{d(off)}$			85	ns
t_f			24	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 V_{DSS}, I_D = I_T$		150	nC
Q_{gs}			40	nC
Q_{gd}			44	nC
R_{thJC}			0.42	$^\circ\text{C/W}$
R_{thCs}		0.15		$^\circ\text{C/W}$

Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$ unless otherwise specified)		
		Min.	Typ.	Max.
I_S	$V_{GS} = 0\text{ V}$			32 A
I_{SM}	Repetitive			70 A
V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$, Pulse test, $t \leq 300\ \mu\text{s}$, duty cycle $d \leq 2\%$			1.5 V
t_{rr}	$I_F = 25\text{ A}, -di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$			250 ns
Q_{RM}			0.8	μC
I_{RM}			6.0	A

Note: Test current $I_T = 16\text{ A}$

ISOPLUS 247 OUTLINE



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - NO CONNECTION

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.

Fig. 1. Output Characteristics
@ 25°C

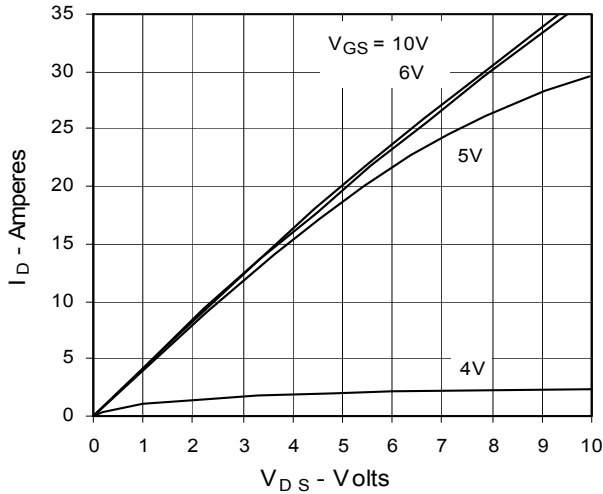


Fig. 2. Extended Output Characteristics
@ 25°C

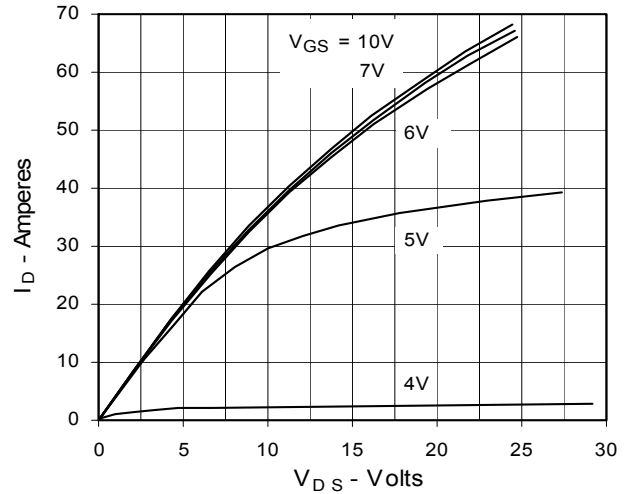


Fig. 3. Output Characteristics
@ 125°C

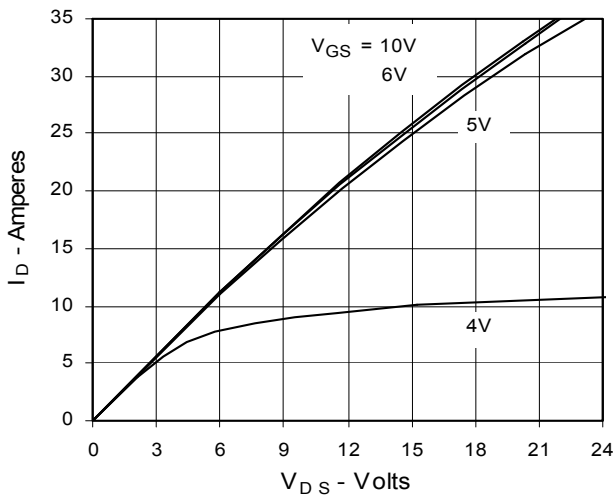


Fig. 4. $R_{DS(on)}$ Normalized to $I_D = 16A$ Value vs. Junction Temperature

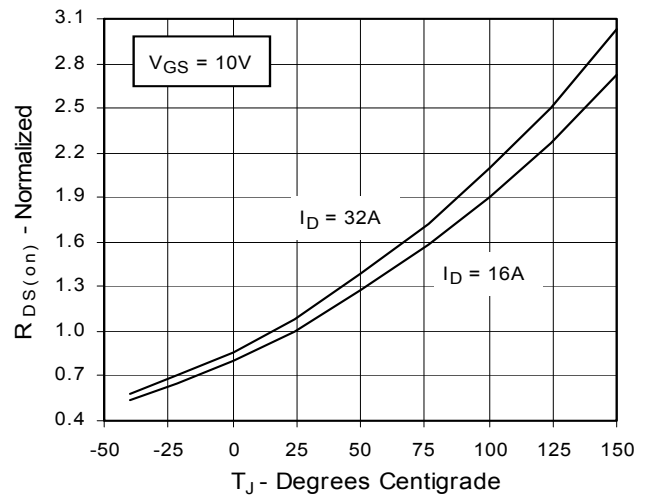


Fig. 5. $R_{DS(on)}$ Normalized to $I_D = 16A$ Value vs. Drain Current

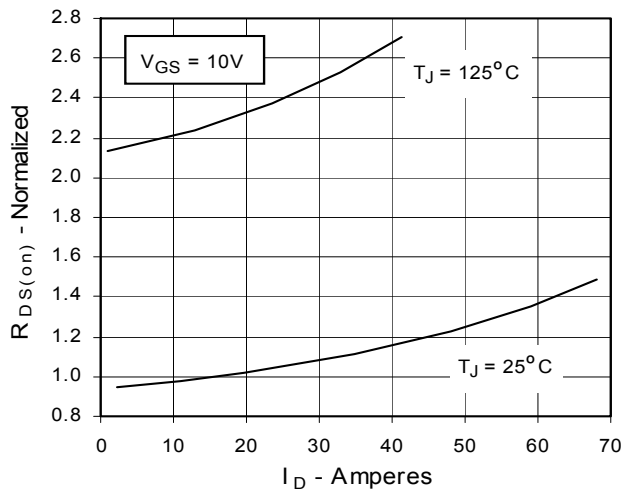


Fig. 6. Drain Current vs. Case Temperature

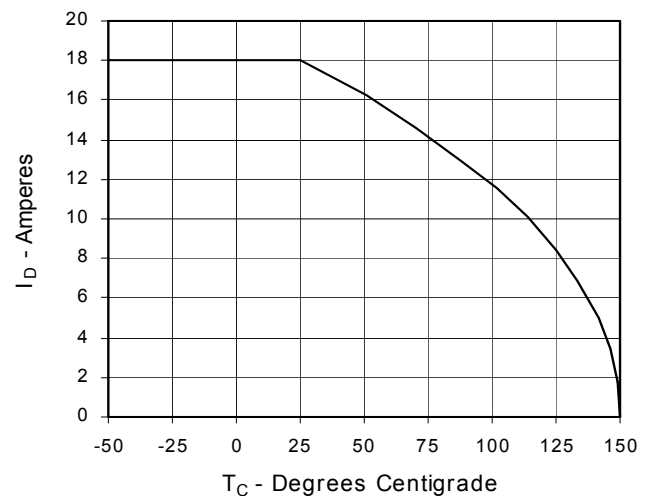


Fig. 7. Input Admittance

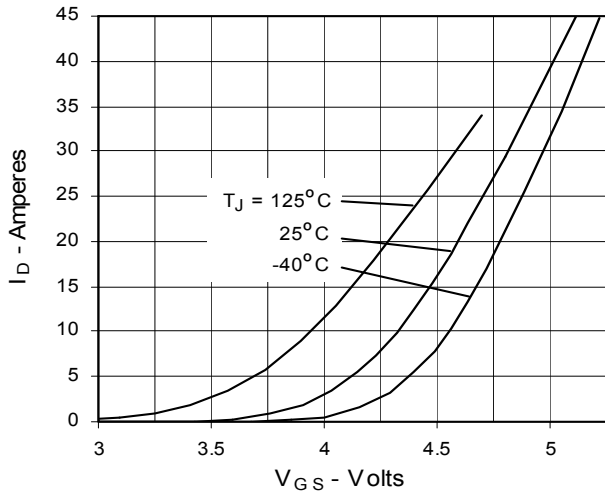


Fig. 8. Transconductance

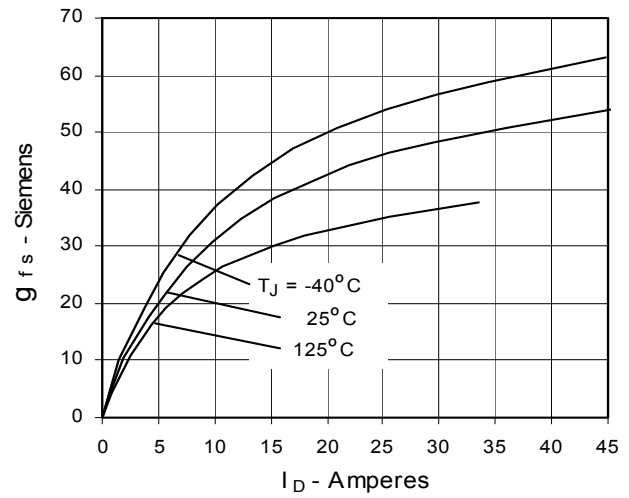


Fig. 9. Source Current vs. Source-To-Drain Voltage

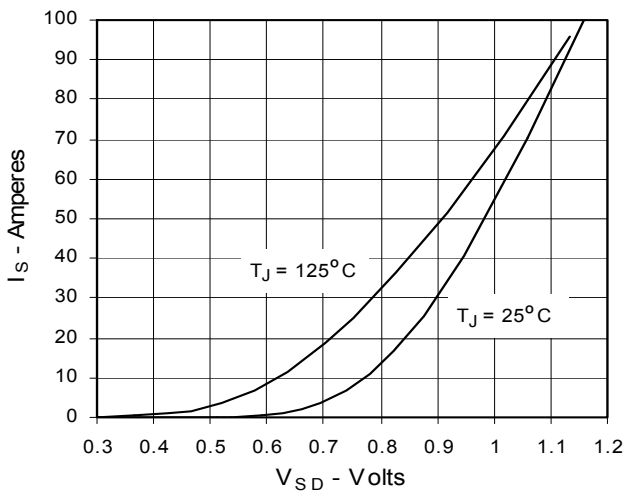


Fig. 10. Gate Charge

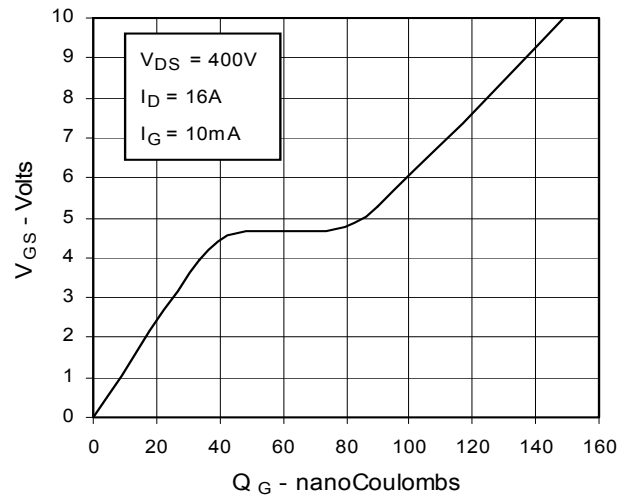


Fig. 11. Capacitance

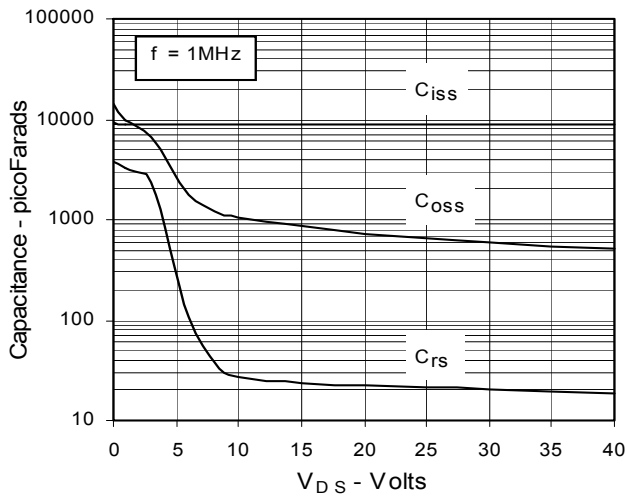


Fig. 12. Maximum Transient Thermal Resistance

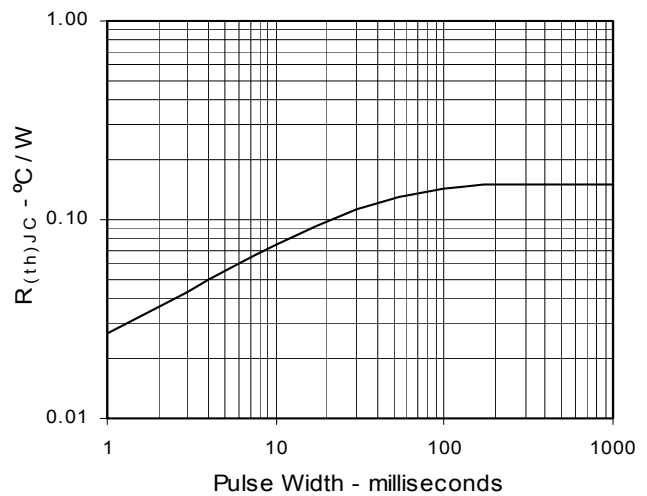


Fig. 13. Maximum Transient Thermal Resistance

